1. General description

NPN high-voltage low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a medium power SOT89 (SC-62) flat lead Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- AEC-Q101 qualified

3. Applications

- · Electronic ballasts
- LED driver for LED chain module
- LCD backlighting
- Automotive motor management
- · Flyback converters
- Switch Mode Power Supply (SMPS)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	500	V
I _C	collector current		-	-	150	mA
h _{FE}	DC current gain	$V_{CE} = 10 \text{ V}; I_{C} = 30 \text{ mA}; T_{amb} = 25 \text{ °C}$	50	100	-	

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		С
2	С	collector		
3	В	base	3 2 1	В — [
			SOT89	sym123



500 V, 150 mA NPN high-voltage low VCEsat (BISS) transistor

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBHV8550X		plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	<u>SOT89</u>			

7. Marking

Table 4. Marking codes

Type number	Marking code
PBHV8550X	C8

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

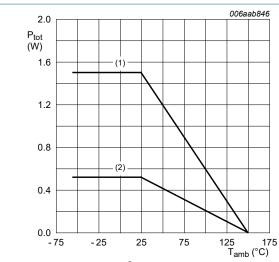
Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	500	V
V_{CEO}	collector-emitter voltage	open base		-	500	V
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V		-	500	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	150	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	0.5	А
I _{BM}	peak base current			-	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	520	mW
			[2]	-	1.5	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

^{1]} Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

PBHV8550X

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 6 cm².

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- (1) FR4 PCB, mounting pad for collector 6 cm²
- (2) FR4 PCB, standard footprint

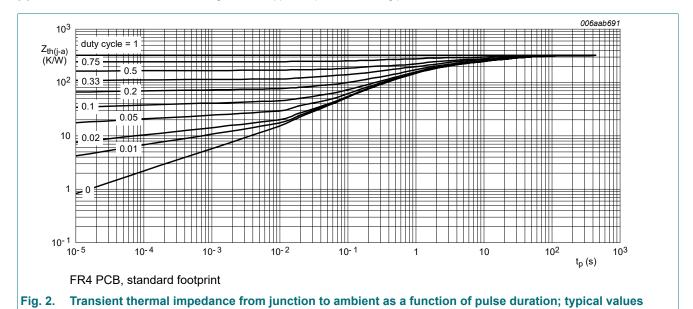
Fig. 1. Power derating curves

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	-	241	K/W
junction to ambient		[2]	-	-	84	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 6 cm².



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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = 100 \ \mu\text{A}; \ I_E = 0 \ \text{A}; \ T_{amb} = 25 \ ^{\circ}\text{C}$	500	-	-	V
V _{(BR)CES}	collector-emitter breakdown voltage (base shorted)	$I_C = 2.5 \text{ mA}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$	500	-	-	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_E = 100 \ \mu A; I_C = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	6	-	-	V
I _{CBO}	collector-base cut-off	V _{CB} = 360 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 360 V; I _E = 0 A; T _j = 150 °C	-	-	50	μΑ
I _{CES}	collector-emitter cut-off current	V _{CE} = 360 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 10 V; I _C = 30 mA; T _{amb} = 25 °C	50	100	-	
		V_{CE} = 10 V; I_{C} = 50 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	50	100	-	
V _{CEsat}	collector-emitter	I _C = 20 mA; I _B = 2 mA; T _{amb} = 25 °C	-	60	75	mV
	saturation voltage	I_C = 50 mA; I_B = 6 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	65	90	mV
V _{BEsat}	base-emitter saturation voltage	I_C = 50 mA; I_B = 5 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.75	0.9	V
t _d	delay time	V _{CC} = 20 V; I _C = 0.05 A; I _{Bon} = 5 mA;	-	80	-	ns
t _r	rise time	I _{Boff} = -5 mA; T _{amb} = 25 °C	-	2700	-	ns
t _{on}	turn-on time		-	2780	-	ns
t _s	storage time		-	3400	-	ns
t _f	fall time		-	800	-	ns
t _{off}	turn-off time		-	4200	-	ns
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 10 mA; f = 100 MHz; T_{amb} = 25 °C	-	35	-	MHz
C _c	collector capacitance	$V_{CB} = 20 \text{ V}; I_{E} = 0 \text{ A}; i_{e} = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 ^{\circ}\text{C}$	-	4	-	pF
C _e	emitter capacitance	V _{EB} = 0.5 V; I _C = 0 A; i _c = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	200	-	pF

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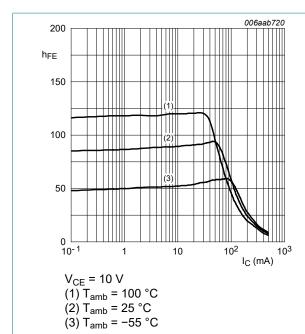


Fig. 3. DC current gain as a function of collector current; typical values

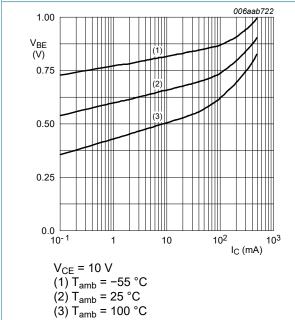


Fig. 5. Base-emitter voltage as a function of collector current; typical values

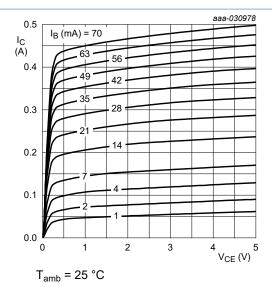
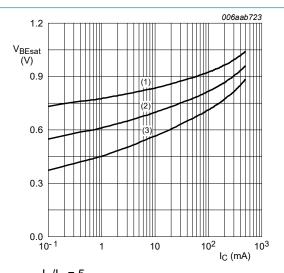


Fig. 4. Collector current as a function of collectoremitter voltage; typical values



 $I_C/I_B = 5$ (1) $T_{amb} = -55$ °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values

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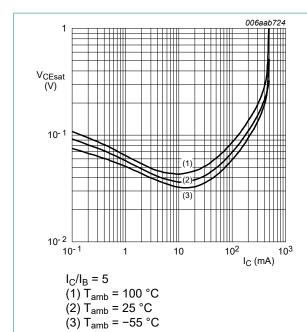


Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

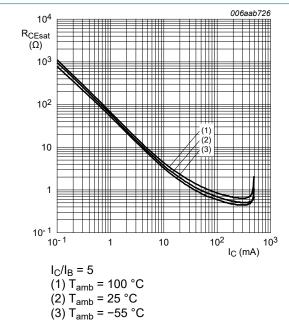


Fig. 9. Collector-emitter saturation resistance as a function of collector current; typical values

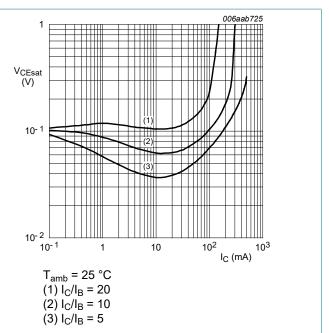


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

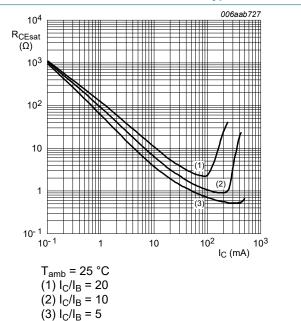
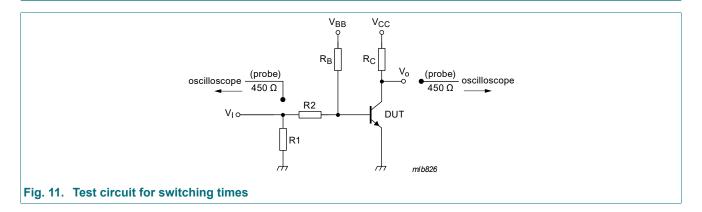


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

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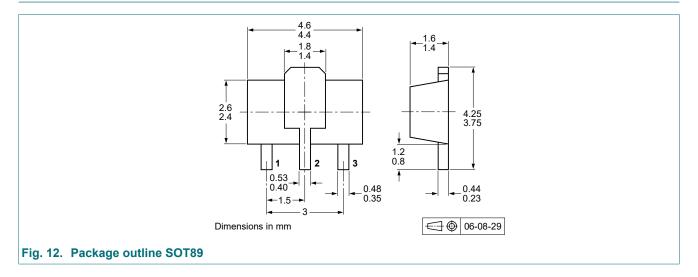
11. Test information



Quality information

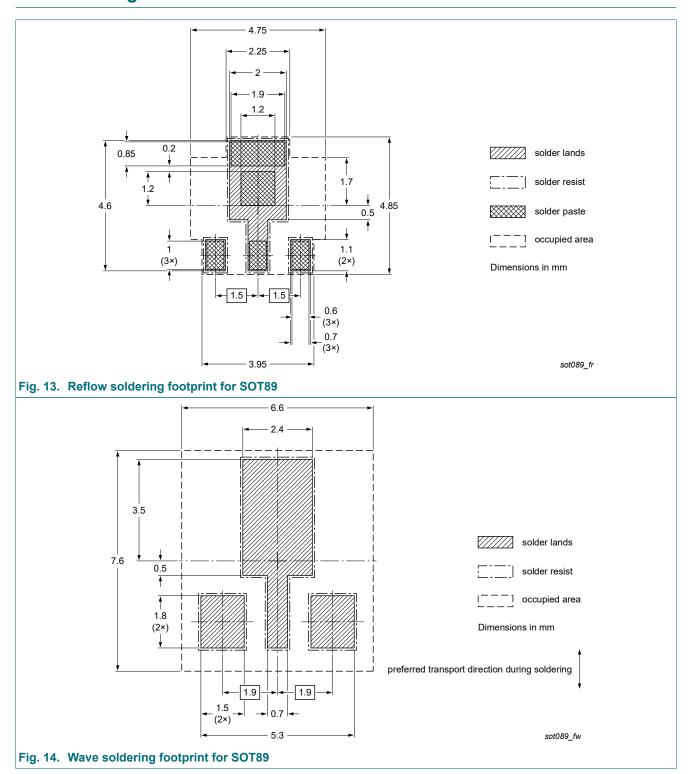
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



500 V, 150 mA NPN high-voltage low VCEsat (BISS) transistor

13. Soldering



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14. Revision history

Table 8. Revision history

Table of Novicion motory							
Release date	Data sheet status	Change notice	Supersedes				
20241009	Product data sheet	-	PBHV8550X v.2				
Figure 1: graph exch	anged						
20200608	Product data sheet	-	PBHV8550X v.2				
20200214	Objective data sheet	-	PBHV8550X v.1				
20200130	Objective data sheet	-	-				
1	Release date 20241009 • Figure 1: graph exch 20200608 20200214	Release date 20241009 Product data sheet Figure 1: graph exchanged 20200608 Product data sheet Objective data sheet	Release date Data sheet status Change notice 20241009 Product data sheet Figure 1: graph exchanged 20200608 Product data sheet Objective data sheet -				

500 V, 150 mA NPN high-voltage low VCEsat (BISS) transistor

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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